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Preface

Although energy dissipation has improved with each new technology node, because SoCs are integrating tens of million devices on-chip, the energy expended per operation has become a critical consideration in digital and analog integrated circuits. The focus of this book is sub-threshold circuit design, which involves scaling voltages below the device thresholds. In this region, the energy per operation can be reduced by an order of magnitude compared to conventional operation but at the cost of circuit performance. In many emerging applications such as self-powered RFID, wireless sensors networks, and portable devices (PDAs, medical monitoring, etc.), the overall battery lifetime is the primary design metric. Sub-threshold design can also be applied to burst mode applications (e.g., a cell-phone processor) where the process spends a significant amount of time in the standby mode. The supply voltage can be reduced to the deep sub-threshold region, dramatically saving power in logic and memory.

Extremely low-power design was first explored in the 1970s for the design of applications such as wristwatch and calculator circuits. Dr. Eric Vittoz pioneered the design and modeling of weak-inversion circuits. In this book, Eric provides his perspective on the evolution of sub-threshold circuit design. Dr. Eric Vittoz and Dr. Christian Enz introduce key models necessary for the design and optimization of weak inversion circuits. Design using weak inversion has been widely adopted in analog circuits, and Eric introduces the key design considerations. His contributions and perspectives are critical to the completeness of this book. We are grateful for his insights.

Ultra-low-voltage CMOS digital operation was demonstrated by Prof. James Meindl and Dr. Richard Swanson in a Journal of Solid-State Circuits paper (April 1972); they predicted CMOS logic operating at a supply voltage of $8kt/q \approx 200$ mV at room temperature and derived the fundamental limits of voltage scaling [1]. This is a key result for low-voltage logic digital design and is an inspiration for many of the results described in this book.

This book focuses on the design of ultra-low-voltage digital circuits (< 0.4V) in scaled technologies. Sub-threshold logic in scaled technology also has

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potential usefulness in high-performance applications. This book introduces the key challenges associated with sub-threshold design including circuit modeling, digital logic design (sizing, logic style selection, optimum supply voltage operation, etc.), memory design, and analog design. In scaled technologies and at low-voltages, the energy contribution due to sub-threshold leakage cannot be ignored. An optimum supply voltage for digital operation is derived that balances leakage and switching energy.

Conventional design approaches for logic scale well into the sub-threshold region, however, proper device sizing is necessary (especially in sequential blocks). The key challenge in the design of ultra-low-voltage digital systems is memory operation. Unfortunately, conventional memory circuits do not easily scale, so new cell-design along with architectures and I/O circuits are required. The energy must be minimized while keeping the cell area overhead to a minimum. This book highlights the importance of design methods that account for process variations, which have a larger impact in low-voltage operation.

The results described in this text book were primarily developed as a part of Ph.D. thesis research at the Massachusetts Institute of Technology [2][3]. The book provides a first step towards the design of ultra-low-voltage circuits. We expect continued development in this area and widespread use of sub-threshold design in many emerging applications.

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Dr. Vittoz has been involved in the formation of the IEEE Solid-State Circuits Society and was a member of its AdCom from 1996 to 1999. He has authored or co-authored more than 140 papers and holds 26 patents in the fields of very lowpower microelectronics, compact transistor modeling, analog CMOS circuit design and biology-inspired analog VLSI. A Life Fellow of the IEEE, he is the recipient of the 2004 IEEE Solid-State Circuits Award.

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